1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32G280 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (⁰C)	Package
EFM32G280F32-QFP100	32	8	32	1.98 - 3.8	-40 - 85	LQFP100
EFM32G280F64-QFP100	64	16	32	1.98 - 3.8	-40 - 85	LQFP100
EFM32G280F128-QFP100	128	16	32	1.98 - 3.8	-40 - 85	LQFP100

Adding the suffix 'T' to the part number (e.g. EFM32G280F32-QFP100T) denotes tray.

Visit **www.silabs.com** for information on global distributors and representatives.

2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32G microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32G280 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32G Reference Manual*.

A block diagram of the EFM32G280 is shown in Figure 2.1 (p. 3) .

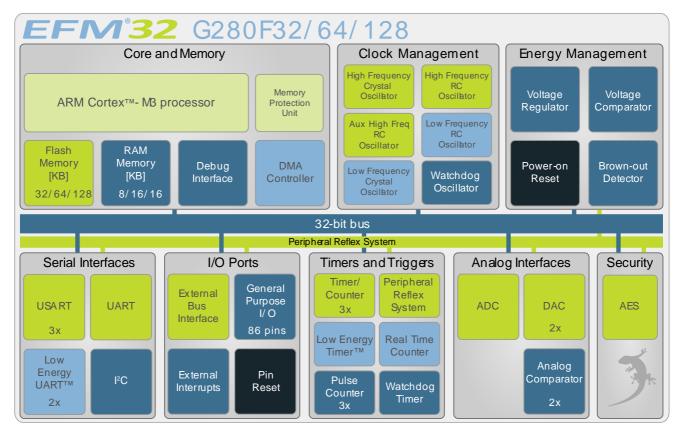


Figure 2.1. Block Diagram

2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32G Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface . In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32G microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is divided

into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32G.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32G microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32G. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 External Bus Interface (EBI)

The External Bus Interface provides access to external parallel interface devices such as SRAM, FLASH, ADCs and LCDs. The interface is memory mapped into the address bus of the Cortex-M3. This enables seamless access from software without manually manipulating the IO settings each time a read or write is performed. The data and address lines are multiplexed in order to reduce the number of pins required to interface the external devices. The timing is adjustable to meet specifications of the external devices. The interface is limited to asynchronous devices.

2.1.11 Inter-Integrated Circuit Interface (I2C)

The I^2C module provides an interface between the MCU and a serial I^2C -bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s.

Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I²C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.

2.1.12 Universal Synchronous/Asynchronous Receiver/Transmitter (US-ART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, and IrDA devices.

2.1.13 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Autobaud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.14 Universal Asynchronous Receiver/Transmitter (UART)

The Universal Asynchronous serial Receiver and Transmitter (UART) is a very flexible serial I/O module. It supports full- and half-duplex asynchronous UART communication.

2.1.15 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUARTTM, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.16 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output. TIMER0 also includes a Dead-Time Insertion module suitable for motor control applications.

2.1.17 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.18 Low Energy Timer (LETIMER)

The unique LETIMERTM, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.19 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.20 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.21 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.22 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.23 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.24 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.25 General Purpose Input/Output (GPIO)

In the EFM32G280, there are 86 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32G280 is a subset of the feature set described in the EFM32G Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M3	Full configuration	NA

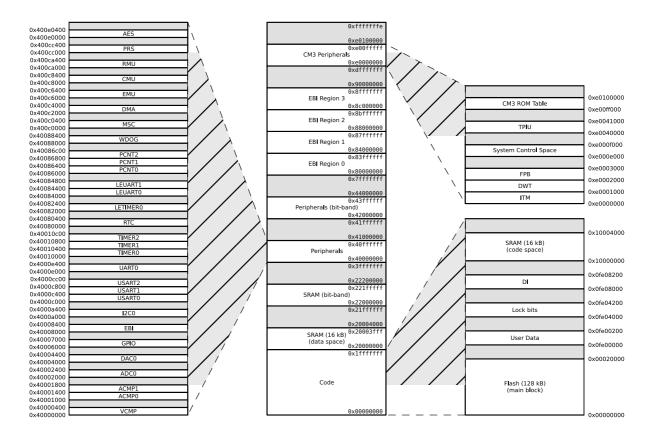
Module	Configuration	Pin Connections
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
СМU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
EBI	Full configuration	EBI_ARDY, EBI_ALE, EBI_WEn, EBI_REn, EBI_CS[3:0], EBI_AD[15:0]
I2C0	Full configuration	12C0_SDA, 12C0_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
RTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 8-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0]
AES	Full configuration	NA
GPIO	86 pins	Available pins are shown in Table 4.3 (p. 55)

2.3 Memory Map

The *EFM32G280* memory map is shown in Figure 2.2 (p. 8), with RAM and Flash sizes for the largest memory configuration.



Figure 2.2. EFM32G280 Memory Map with largest RAM and Flash sizes



3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}C$ and $V_{DD}=3.0$ V, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 9) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 9).

Symbol	Parameter	Condition	Min	Тур	Max	Unit
T _{STG}	Storage tempera- ture range		-40		150 ¹	°C
T _S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V _{DDMAX}	External main sup- ply voltage		0		3.8	V
V _{IOPIN}	Voltage on any I/O pin		-0.3		V _{DD} +0.3	V
1	Current per I/O pin (sink)				100	mA
I _{IOMAX}	Current per I/O pin (source)				-100	mA

Table 3.1. Absolute Maximum Ratings

¹Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Тур	Max	Unit
T _{AMB}	Ambient temperature range	-40		85	°C
V _{DDOP}	Operating supply voltage	1.98		3.8	V
f _{APB}	Internal APB clock frequency			32	MHz
f _{AHB}	Internal AHB clock frequency			32	MHz

3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
Symbol I _{EMO}		32 MHz HFXO, all peripheral clocks disabled, V_{DD} = 3.0 V		180		μΑ/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		181	206	μΑ/ MHz
	EM0 current. No prescaling. Running	21 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		183	207	μΑ/ MHz
I _{EMO}	prime number cal- culation code from Flash. (Production	14 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		185	211	µA/ MHz
	test condition = 14 MHz)	11 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		186	215	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		191	218	µA/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		220		µA/ MHz
		32 MHz HFXO, all peripheral clocks disabled, V_{DD} = 3.0 V		45		µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		47	62	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V	I 48 6	64	μΑ/ MHz	
I _{EM1}	EM1 current (Pro- duction test condi- tion = 14 MHz)	14 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		50	69	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		51		μΑ/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		56	83	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD} = 3.0 V		103		μΑ/ MHz
	EM2 surrest	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =25°C		0.9	1.5	μΑ
I _{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =85°C		3.0	6.0	μA
I=	EM3 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.59	1.0	μA
I _{EM3}		V _{DD} = 3.0 V, T _{AMB} =85°C		2.75	5.8	μA
I =	EM4 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.02	0.045	μA
I _{EM4}		V _{DD} = 3.0 V, T _{AMB} =85°C		0.25	0.7	μA

3.4.1 EM0 Current Consumption

Figure 3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 28 MHz

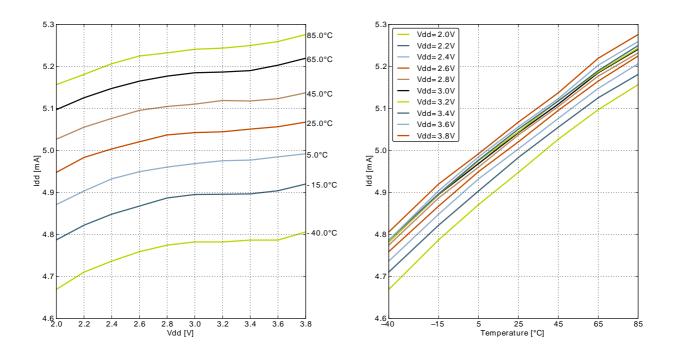


Figure 3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21 MHz

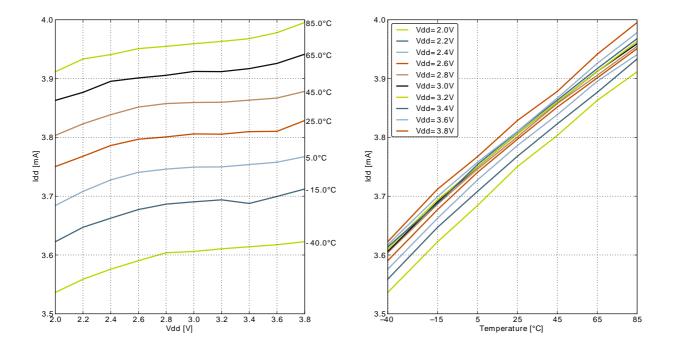


Figure 3.3. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 14 MHz

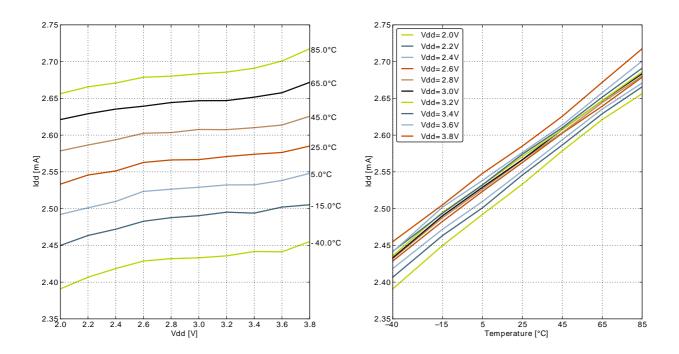


Figure 3.4. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 11 MHz

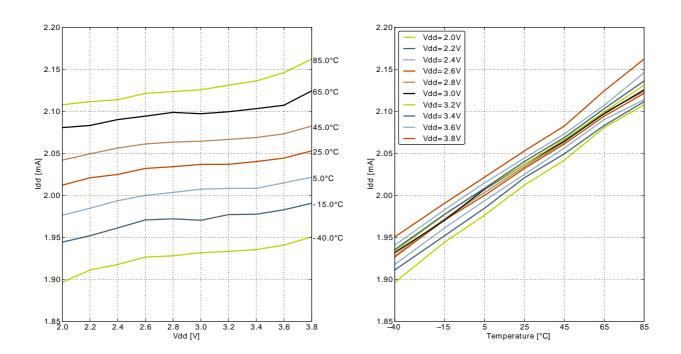
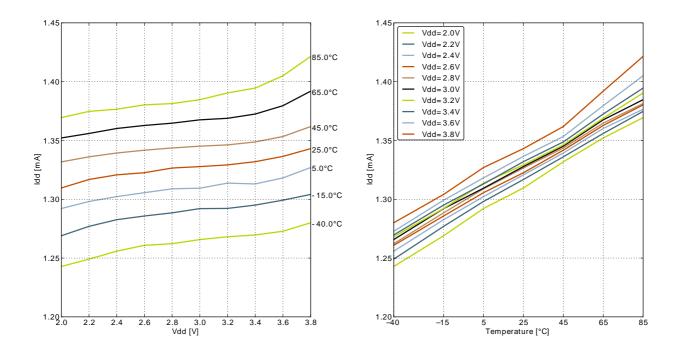
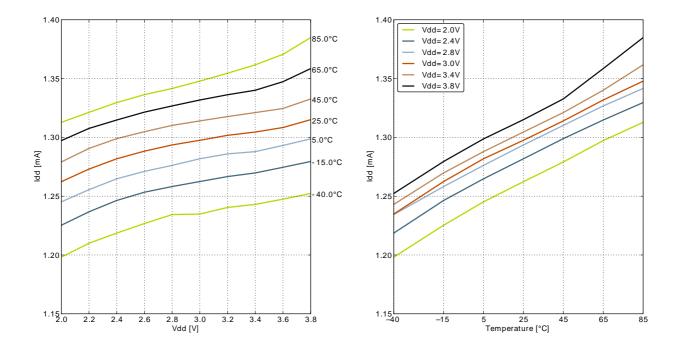


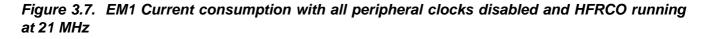
Figure 3.5. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 7 MHz



3.4.2 EM1 Current Consumption

Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28 MHz





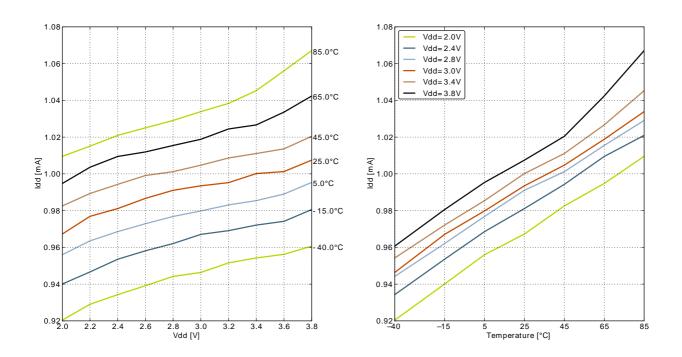
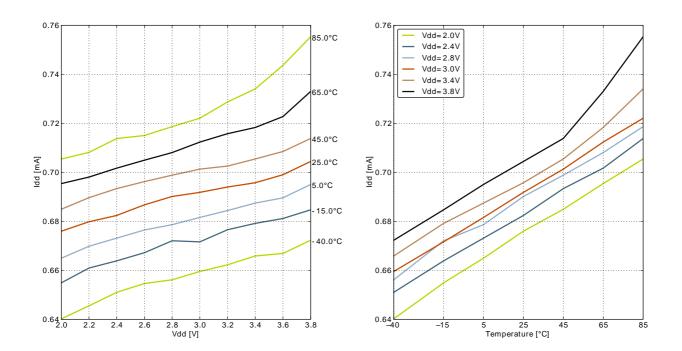
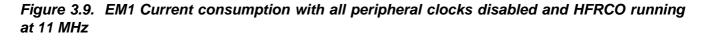


Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz





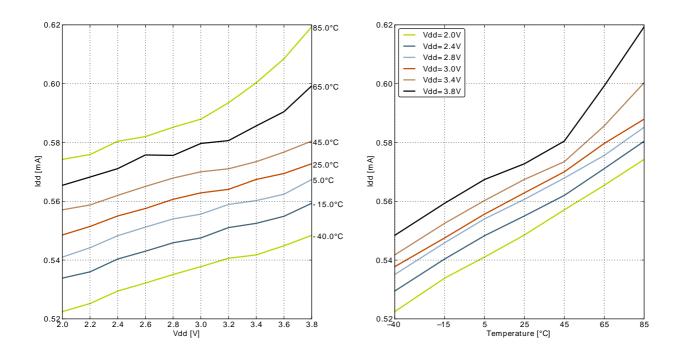
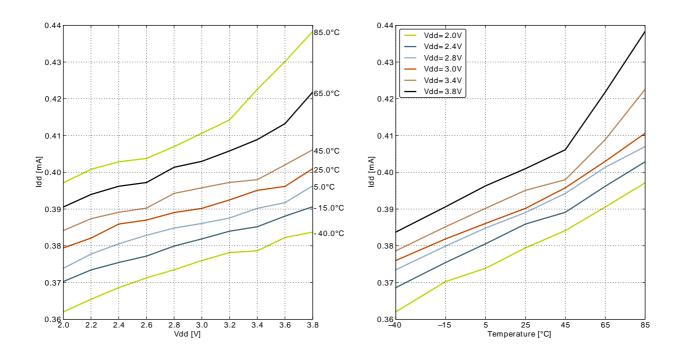
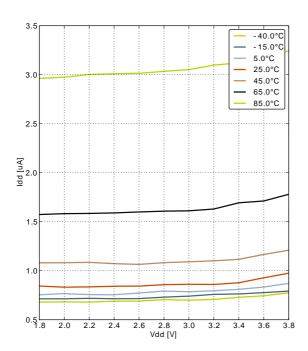


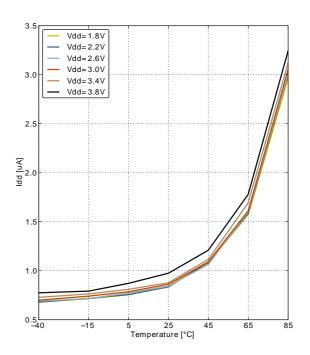
Figure 3.10. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 7 MHz



3.4.3 EM2 Current Consumption

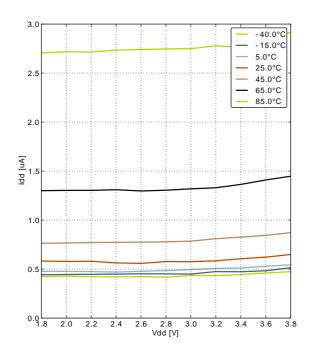
Figure 3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.

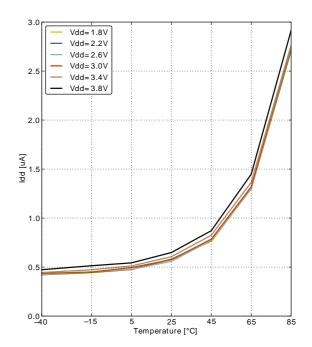




3.4.4 EM3 Current Consumption

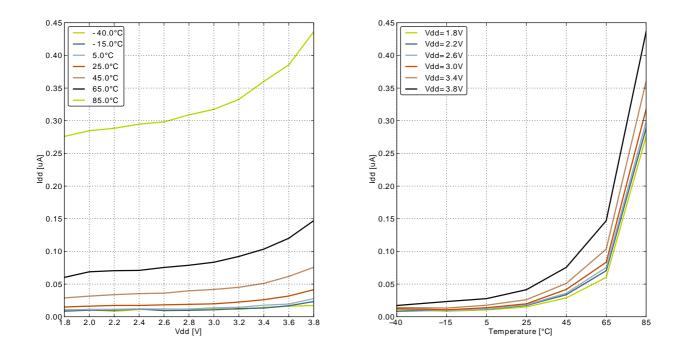
Figure 3.12. EM3 current consumption.





3.4.5 EM4 Current Consumption





3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4.	Energy	Modes	Transitions
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Symbol	Parameter	Min	Тур	Max	Unit
t _{EM10}	Transition time from EM1 to EM0		0		HF- CORE- CLK cycles
t _{EM20}	Transition time from EM2 to EM0		2		μs
t _{EM30}	Transition time from EM3 to EM0		2		μs
t _{EM40}	Transition time from EM4 to EM0		163		μs

3.6 Power Management

The EFM32G requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{BODextthr} -	BOD threshold on falling external sup- ply voltage		1.74		1.96	V
V _{BODextthr+}	BOD threshold on rising external sup- ply voltage			1.85		V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external sup- ply voltage				1.98	V
t _{RESETdly}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
t _{RESET}	negative pulse length to ensure complete reset of device		50			ns
C _{DECOUPLE}	Voltage regulator decoupling capaci- tor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Тур	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
		T _{AMB} <150°C	10000			h
RET _{FLASH}	Flash data retention	T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) pro- gramming time		20			μs
t _{P_ERASE}	Page erase time		20	20.4	20.8	ms
t _{D_ERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ¹	mA
V _{FLASH}	Supply voltage dur- ing flash erase and write		1.98		3.8	V

¹Measured at 25°C

3.8 General Purpose Input Output

Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V _{IOIL}	Input low voltage				0.30V _{DD} ¹	V



Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{IOIH}	Input high voltage		0.70V _{DD} ¹			V
		Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
V _{IOOH}	Output high volt- age (Production test condition = 3.0V,	Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
VIOOH	DRIVEMODE = STANDARD)	Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
		Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
N/	Output low voltage (Production test	Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
V _{IOOL}	condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V
		Sinking 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V _{DD}	V
IOLEAK	Input leakage cur- rent	High Impedance IO connected to GROUND or V _{DD}		±0.1	±40	nA

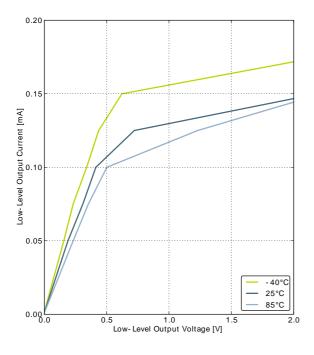


Symbol	Parameter	Condition	Min	Тур	Max	Unit
R _{PU}	I/O pin pull-up resis- tor			40		kOhm
R _{PD}	I/O pin pull-down re- sistor			40		kOhm
R _{IOESD}	Internal ESD series resistor			200		Ohm
t _{IOGLITCH}	Pulse width of puls- es to be removed by the glitch sup- pression filter		10		50	ns
t _{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capaci- tance C_L =12.5-25pF.	20+0.1C _L		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C _L =350-600pF	20+0.1C _L		250	ns
V _{IOHYST}	I/O pin hysteresis (V _{IOTHR+} - V _{IOTHR-})	V _{DD} = 1.98 - 3.8 V	0.1V _{DD}			V

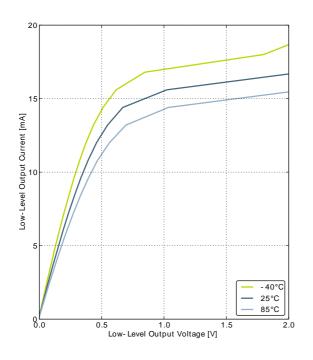
¹If the GPIO input voltage is between $0.3V_{DD}$ and $0.7V_{DD}$, the current consumption will increase.



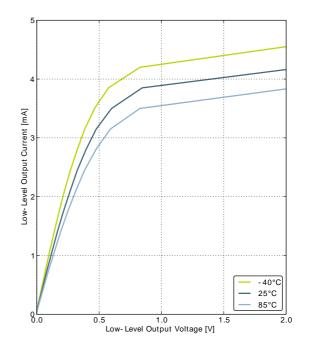
Figure 3.14. Typical Low-Level Output Current, 2V Supply Voltage



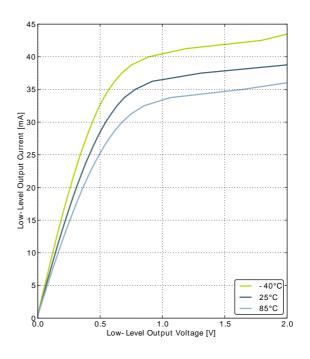
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD



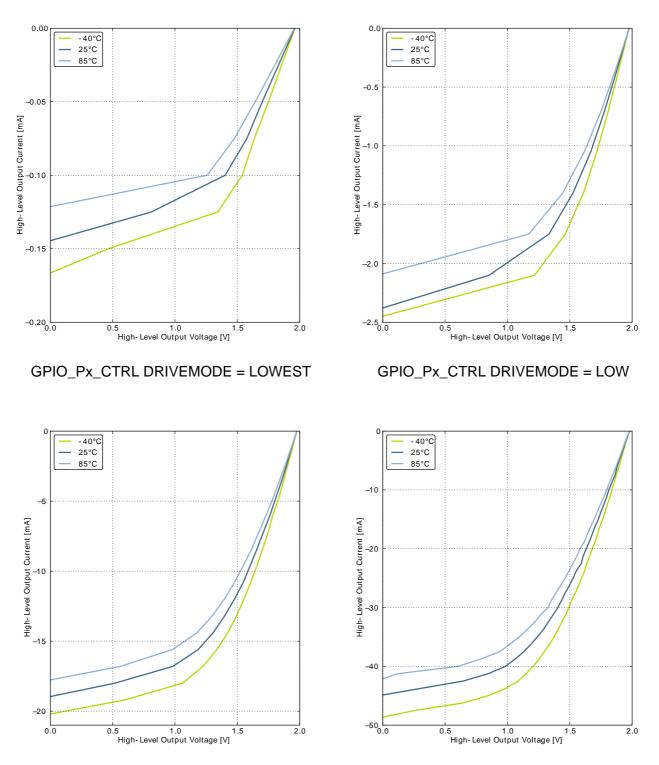
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.15. Typical High-Level Output Current, 2V Supply Voltage

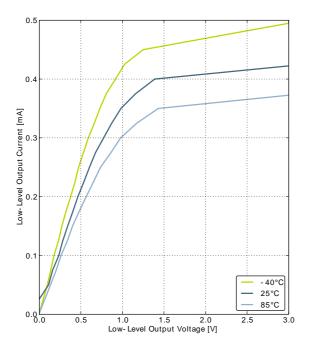


GPIO_Px_CTRL DRIVEMODE = STANDARD

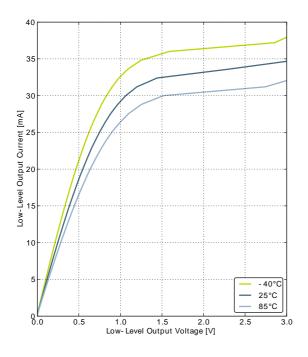
GPIO_Px_CTRL DRIVEMODE = HIGH



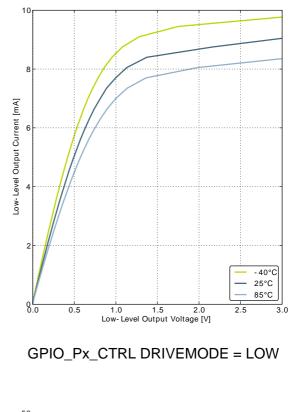
Figure 3.16. Typical Low-Level Output Current, 3V Supply Voltage

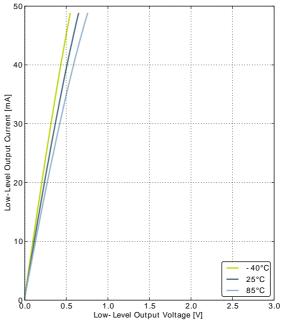


GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD

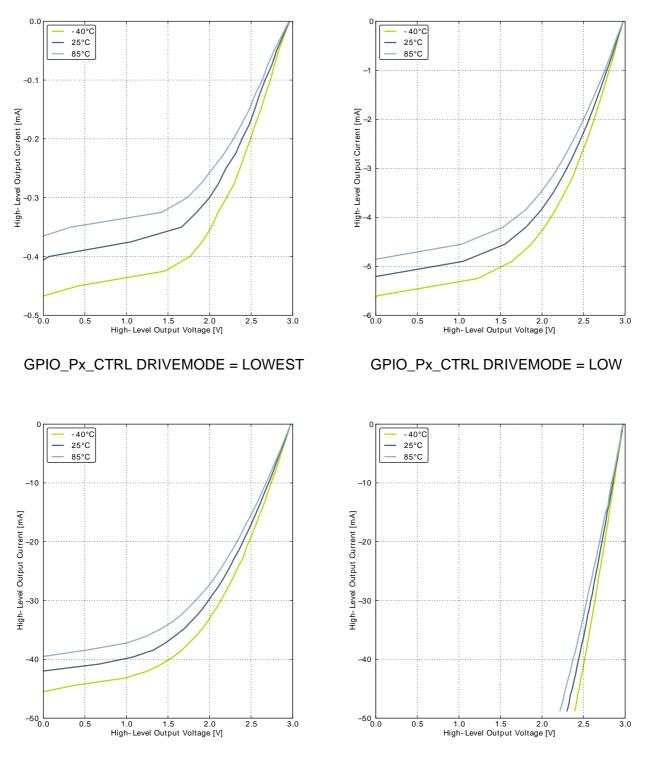




GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.17. Typical High-Level Output Current, 3V Supply Voltage

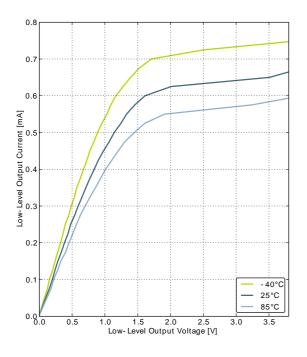


GPIO_Px_CTRL DRIVEMODE = STANDARD

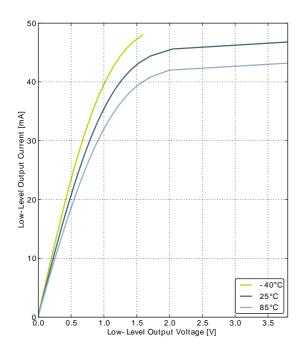




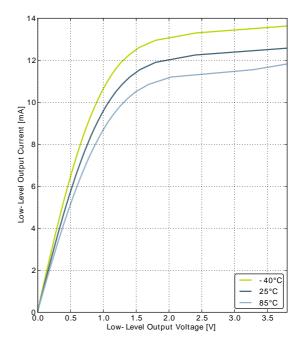
Figure 3.18. Typical Low-Level Output Current, 3.8V Supply Voltage



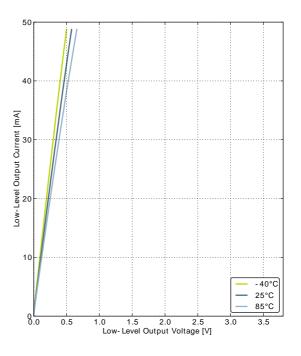
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD



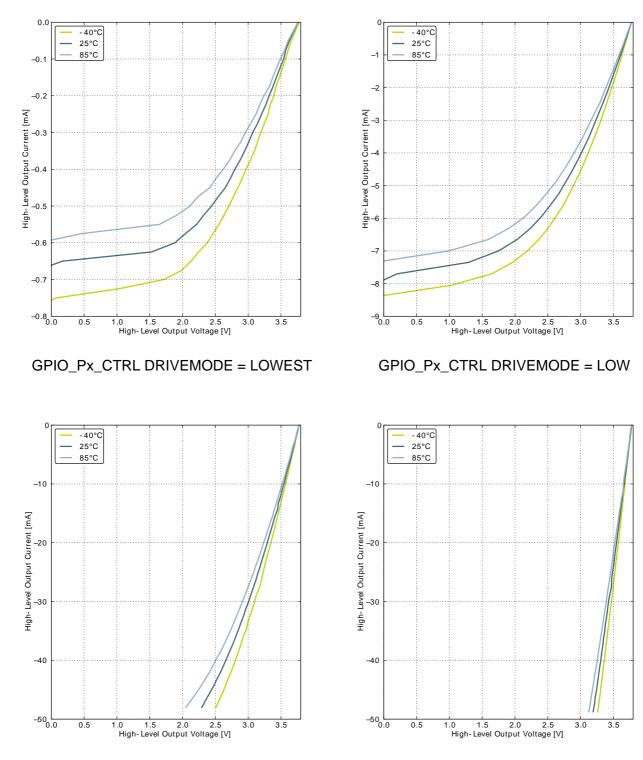
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = STANDARD



3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR _{LFXO}	Supported crystal equivalent series re- sistance (ESR)			30	120	kOhm
C _{LFXOL}	Supported crystal external load range		X ¹		25	pF
I _{LFXO}	Current consump- tion for core and buffer after startup.	ESR=30 kOhm, C _L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t _{LFXO}	Start- up time.	ESR=30 kOhm, C _L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in Configurator in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

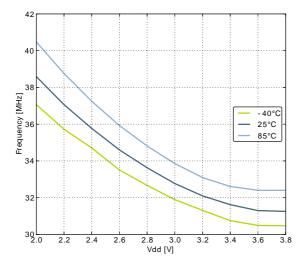
Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{HFXO}	Supported nominal crystal Frequency		4		32	MHz
500	Supported crystal	Crystal frequency 32 MHz		30	60	Ohm
ESR _{HFXO}	equivalent series re- sistance (ESR)	Crystal frequency 4 MHz	432quency 32 MHz30quency 4 MHz400DST in CMU_CTRL201120SR=400 Ohm, HFXOBOOST in RL equals 0b1185SR=30 Ohm, HFXOBOOST in 	Ohm		
g _m HFxO	The transconduc- tance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C _{HFXOL}	Supported crystal external load range		5		25	pF
1	Current consump- tion for HFXO after startup	4 MHz: ESR=400 Ohm, $C_L=20 \text{ pF}$, HFXOBOOST in CMU_CTRL equals 0b11		85		μA
I _{HFXO}		32 MHz: ESR=30 Ohm, $C_L=10 \text{ pF}$, HFXOBOOST in CMU_CTRL equals 0b11		165		μA
	Startup time	32 MHz: ESR=30 Ohm, $C_L=10 \text{ pF}$, HFXOBOOST in CMU_CTRL equals 0b11		400		μs
t _{HFXO}	Pulse width re- moved by glitch de- tector		1		4	ns

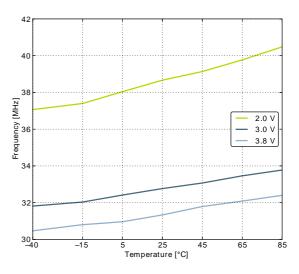
3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFRCO}	Oscillation frequen- cy , V_{DD} = 3.0 V, T_{AMB} =25°C		31.29	32.768	34.24	kHz
t _{LFRCO}	Startup time not in- cluding software calibration			150		μs
I _{LFRCO}	Current consump- tion			190		nA
TC _{LFRCO}	Temperature coeffi- cient			±0.02		%/°C
VC _{LFRCO}	Supply voltage co- efficient			±15		%/V
TUNESTEP _L FRCO	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage





3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		28 MHz frequency band	27.16	28	28.84	MHz
		21 MHz frequency band	20.37	21	21.63	MHz
4	Oscillation frequen-	14 MHz frequency band	13.58	14	14.42	MHz
f _{HFRCO}	cy, V _{DD} = 3.0 V, T _{AMB} =25°C	11 MHz frequency band	10.67	11	11.33	MHz
		7 MHz frequency band	6.402	6.6 ¹	6.798	MHz
		1 MHz frequency band	1.164	1.2 ²	1.236	MHz
	Settling time after start-up	f _{HFRCO} = 14 MHz		0.6		Cycles
t _{HFRCO_settling}	Settling time after band switch			25		Cycles
		f _{HFRCO} = 28 MHz		106	190	μA
		f _{HFRCO} = 21 MHz		93	155	μA
1	Current consump-	f _{HFRCO} = 14 MHz		77	120	μA
I _{HFRCO}	tion (Production test condition = 14 MHz)	f _{HFRCO} = 11 MHz		72	110	μA
		f _{HFRCO} = 6.6 MHz		63	90	μA
		f _{HFRCO} = 1.2 MHz		22	32	μA
DC _{HFRCO}	Duty cycle	f _{HFRCO} = 14 MHz	48.5	50	51	%
TUNESTEP _{H-} FRCO	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.



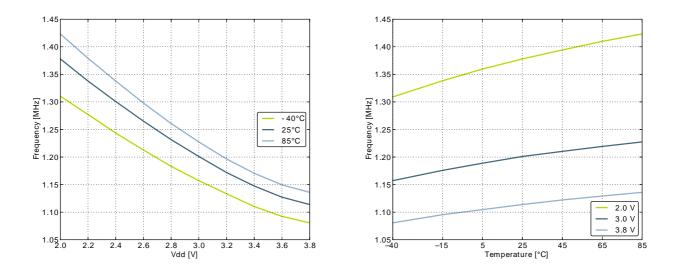


Figure 3.22. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

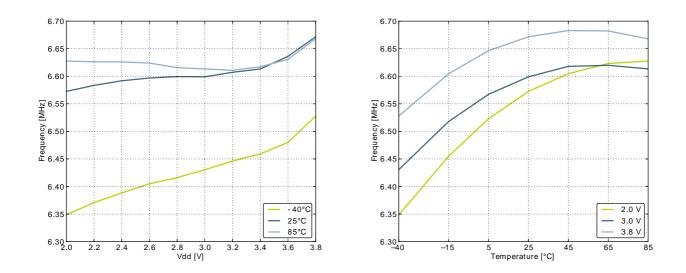
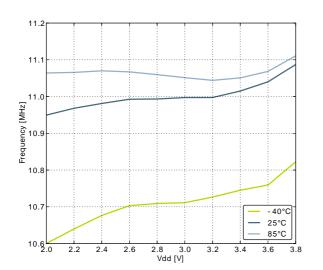


Figure 3.23. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature



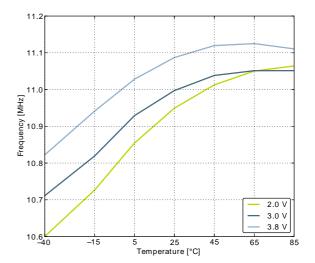




Figure 3.24. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

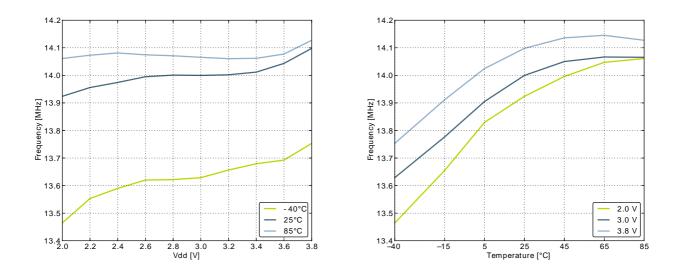


Figure 3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

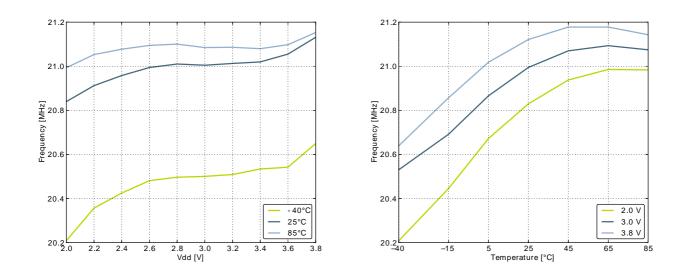
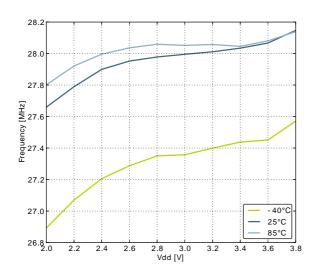
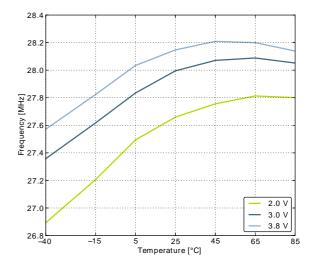


Figure 3.26. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature





3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
fauxhfrco	Oscillation frequen- cy, V_{DD} = 3.0 V, T_{AMB} =25°C	14 MHz frequency band	13.580	14.0	14.420	MHz
t _{AUXHFRCO_settlir}	_g Settling time after start-up	f _{AUXHFRCO} = 14 MHz		0.6		Cycles
DC _{AUXHFRCO}	Duty cycle	f _{AUXHFRCO} = 14 MHz	48.5	50	51	%
TUNESTEP _{AU}	Frequency step for LSB change in TUNING value			0.3 ¹		%

¹The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value in the 14 MHz range across operating conditions.

3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{ULFRCO}	Oscillation frequen- cy	25°C, 3V	0.70		1.75	kHz
TC _{ULFRCO}	Temperature coeffi- cient			0.05		%/°C
VC _{ULFRCO}	Supply voltage co- efficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

Symbol	Parameter	Condition	Min	Тур	Max	Unit
	Input voltage range	Single ended	0		V _{REF}	V
V ADCIN		Differential	-V _{REF} /2		V _{REF} /2	V
V _{ADCREFIN}	Input range of exter- nal reference volt- age, single ended and differential		1.25		V _{DD}	V
V _{ADCREFIN_CH7}	Input range of ex- ternal negative ref- erence voltage on channel 7	See V _{ADCREFIN}	0		V _{DD} - 1.1	V
V _{ADCREFIN_CH6}	Input range of ex- ternal positive ref- erence voltage on channel 6	See V _{ADCREFIN}	0.625		V _{DD}	V
V _{ADCCMIN}	Common mode in- put range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA



Symbol	Parameter	Condition	Min	Тур	Max	Unit
CMRR _{ADC}	Analog input com- mon mode rejection ratio			65		dB
		1 MSamples/s, 12 bit, external reference		351		μA
		1 MSamples/s, 12 bit, internal reference		411		μA
I _{ADC}	Average active cur-	10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b00, ADC_CLK running at 13MHz		67		μA
	rent	10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b01, ADC_CLK running at 13MHz		63		μΑ
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b10, ADC_CLK running at 13MHz		64		μA
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFILT}	Input RC filter resis- tance			10		kOhm
C _{ADCFILT}	Input RC filter/de- coupling capaci- tance			250		fF
f _{ADCCLK}	ADC Clock Fre- quency				13	MHz
		6 bit	7			ADC- CLK Cycles
t _{ADCCONV}	Conversion time	8 bit	11			ADC- CLK Cycles
		12 bit	13			ADC- CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC- CLK Cycles
t _{ADCACQVDD3}	Required acquisi- tion time for VDD/3 reference		2			μs
tadcstart	Startup time of ref- erence generator and ADC core in NORMAL mode			5		μs
	Startup time of ref- erence generator and ADC core in			1		μs



Symbol	Parameter	Condition	Min	Тур	Мах	Unit
	KEEPADCWARM mode					
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
		1 MSamples/s, 12 bit, differen- tial, V _{DD} reference		67		dB
	Signal to Noise Ra-	1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		69		dB
SNR _{ADC}	tio (SNR)	200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, V _{DD} reference	63	69		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		70		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
SINAD _{ADC}	SIgnal-to-Noise And Distortion-ratio	1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
	(SINAD)	1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		68		dB
		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, V _{DD} reference	62	68		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		69		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
SFDR _{ADC}	Spurious-Free Dy- namic Range (SF- DR)	1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		75		dBc
		1 MSamples/s, 12 bit, differen- tial, 5V reference		69		dBc
		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		79		dBc



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		200 kSamples/s, 12 bit, differ- ential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		79		dBc
M	Offect veltage	After calibration, single ended	-4	0.3	4	mV
VADCOFFSET	Offset voltage	After calibration, differential		0.3		mV
	Thermometer out- put gradient			-1.92		mV/°C
TGRAD _{ADCTH}				-6.3		ADC Codes/ °C
DNL _{ADC}	Differential non-lin- earity (DNL)	V_{DD} = 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL _{ADC}	Integral non-linear- ity (INL), End point method	V_{DD} = 3.0 V, external 2.5V reference		±1.2	±3	LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits

¹On the average every ADC will have one missing code, most likely to appear around $2048 \pm n^{*}512$ where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.27 (p. 36) and Figure 3.28 (p. 37), respectively.

Figure 3.27. Integral Non-Linearity (INL)

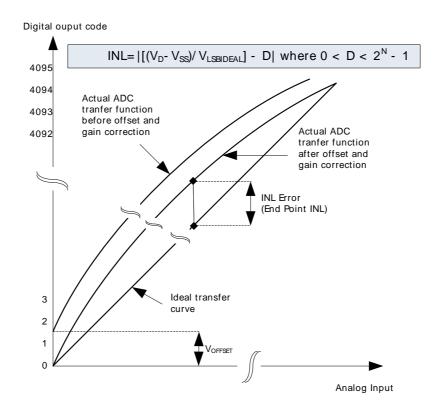
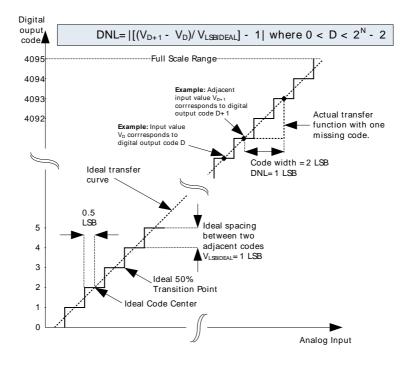


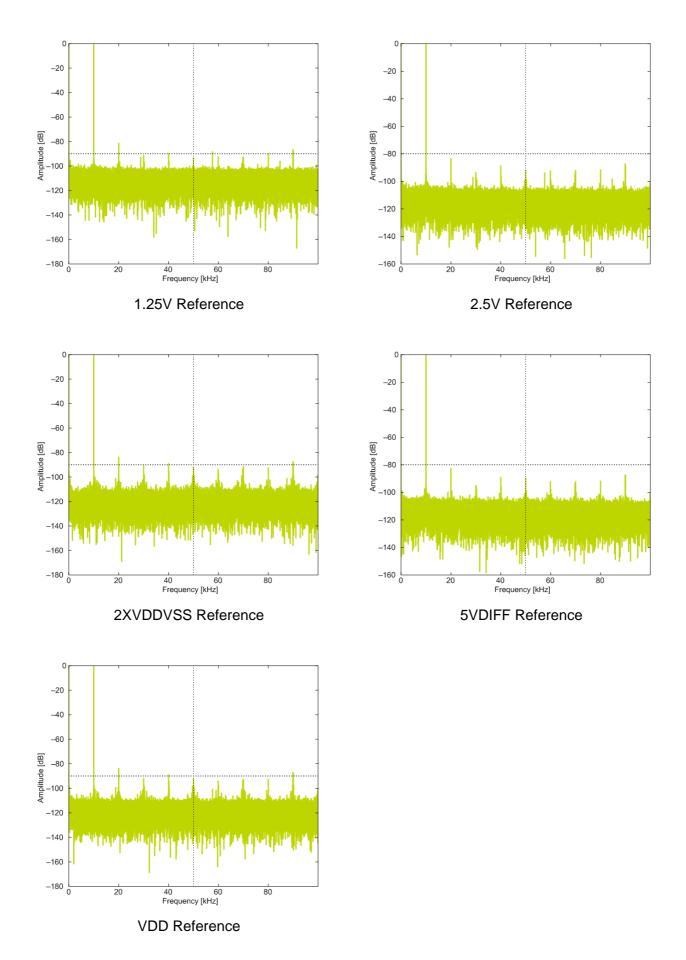


Figure 3.28. Differential Non-Linearity (DNL)



3.10.1 Typical performance

Figure 3.29. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



3072

3072

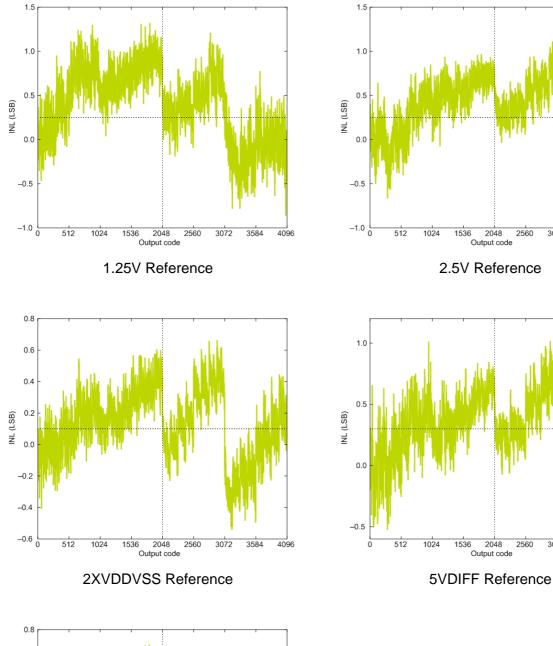
3584

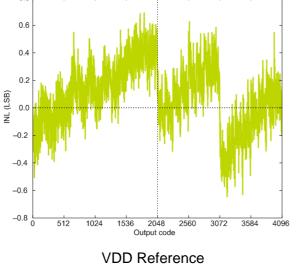
4096

3584

4096

Figure 3.30. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C





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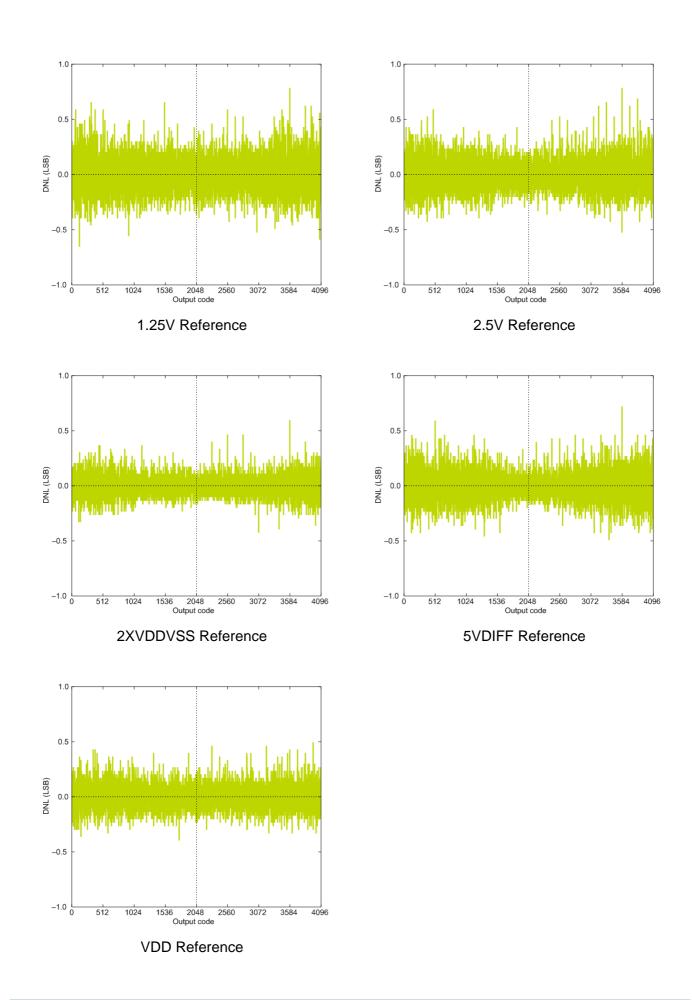


Figure 3.32. ADC Absolute Offset, Common Mode = Vdd /2

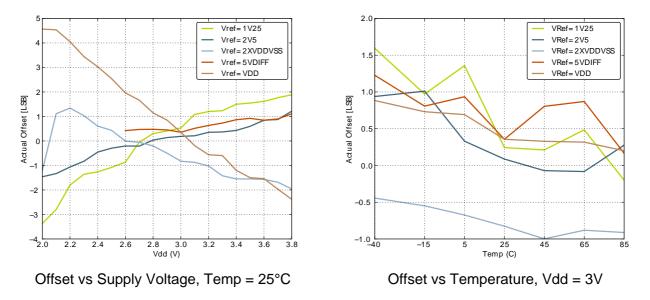
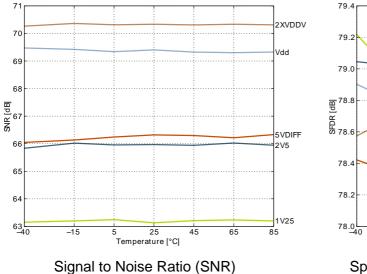
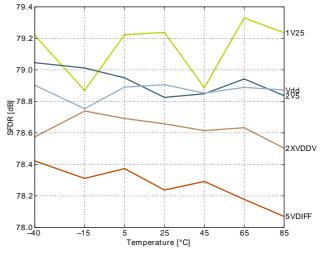


Figure 3.33. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V





Spurious-Free Dynamic Range (SFDR)

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Тур	Max	Unit
M	Output voltage	VDD voltage reference, single ended	0		V _{DD}	V
V _{DACOUT}	range	VDD voltage reference, differ- ential	-V _{DD}		V _{DD}	V
V _{DACCM}	Output common mode voltage range		0		V _{DD}	V
	Active current in-	500 kSamples/s, 12bit		400 ¹	650	μA
I _{DAC}	cluding references	100 kSamples/s, 12 bit		200 ¹	250	μA
	for 2 channels	1 kSamples/s 12 bit		17 ¹	25	μA



Symbol	Parameter	Condition	Min	Тур	Max	Unit
SR _{DAC}	Sample rate				500	ksam- ples/s
		Continuous Mode			1000	kHz
f _{DAC}	DAC clock frequen-	Sample/Hold Mode			250	ksam- kHz kHz kHz u u u d d d d d d d d d d d d d d d d
		Sample/Off Mode			250	kHz
CYC _{DACCONV}	Clock cyckles per conversion			2		
t _{DACCONV}	Conversion time		2			μs
t _{DACSETTLE}	Settling time			5		μs
		500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
SNR _{DAC}	Signal to Noise Ra- tio (SNR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
		500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		57		dB
	Signal to Noise-	500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
SNDR _{DAC}	pulse Distortion Ra- tio (SNDR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		56		
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
		500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dBc
	Spurious-Free	500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
SFDR _{DAC}	Dynamic Range(SFDR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		61		ples/s kHz kHz µs dB dB dB dB dB dB dB dB dB dB dB dB dB
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		55		
		500 kSamples/s, 12 bit, differ- ential, V _{DD} reference		60		dBc
\/	0#==+== !!	After calibration, single ended		2		mV
VDACOFFSET	Offset voltage	After calibration, differential		2		mV
VDACSHMDRIFT	Sample-hold mode voltage drift			540		µV/ms



Symbol	Parameter	Condition	Min	Тур	Max	Unit
DNL _{DAC}	Differential non-lin- earity			±1		LSB
INL _{DAC}	Integral non-lineari- ty			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹Measured with a static input code and no loading on the output.

3.12 Analog Comparator (ACMP)

Table 3.16. ACMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ACMPIN}	Input voltage range		0		V _{DD}	V
V _{ACMPCM}	ACMP Common Mode voltage range		0		V _{DD}	V
		BIASPROG=0b0000, FULL- BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		55	600	nA
I _{ACMP}	Active current	BIASPROG=0b1111, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.82	12	μA
		BIASPROG=0b1111, FULL- BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	μA
	Current consump-	Internal voltage reference off. Using external voltage refer- ence		0	0.5	μA
I _{ACMPREF}	tion of internal volt- age reference	Internal voltage reference, LPREF=1		0.050	3	μA
		Internal voltage reference, LPREF=0		6		μA
VACMPOFFSET	Offset voltage	BIASPROG= 0b1010, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
V _{ACMPHYST}	ACMP hysteresis	Programmable		17		mV
		CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
D	Capacitive Sense	CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
R _{CSRES}	Internal Resistance	CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
t _{ACMPSTART}	Startup time				10	μs

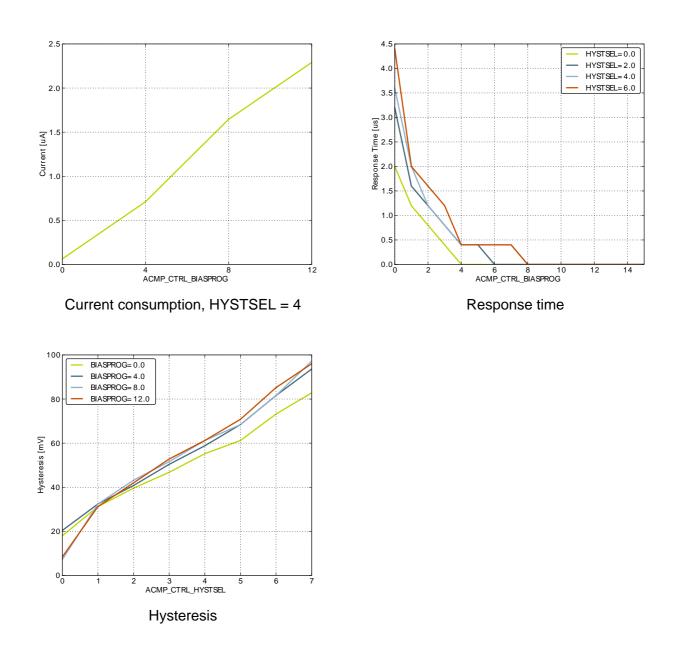
The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 43). $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current



(3.1)

Figure 3.34. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



3.13 Voltage Comparator (VCMP)

Table 3.17. VCMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{VCMPIN}	Input voltage range			V _{DD}		V
V _{VCMPCM}	VCMP Common Mode voltage range			V _{DD}		V
1	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	1	μA
IVCMP	Active current	BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	30	μA
t _{VCMPREF}	Startup time refer- ence generator	NORMAL		10		μs
V	Offect veltage	Single ended		10		mV
V _{VCMPOFFSET}	T Offset voltage	Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			17		mV
t _{VCMPSTART}	Startup time				10	μs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

V_{DD Trigger Level}=1.667V+0.034 ×TRIGLEVEL

3.14 I2C

Table 3.18. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Тур	Мах	Unit
f _{SCL}	SCL clock frequency	0		100 ¹	kHz
t _{LOW}	SCL clock low time	4.7			μs
t _{HIGH}	SCL clock high time	4.0			μs
t _{SU,DAT}	SDA set-up time	250			ns
t _{HD,DAT}	SDA hold time	8		3450 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	4.7			μs
t _{HD,STA}	(Repeated) START condition hold time	4.0			μs
t _{SU,STO}	STOP condition set-up time	4.0			μs
t _{BUF}	Bus free time between a STOP and START condition	4.7			μs

¹For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32G Reference Manual. ²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 4).

(3.2)

Table 3.19. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			μs
t _{HIGH}	SCL clock high time	0.6			μs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			μs
t _{HD,STA}	(Repeated) START condition hold time	0.6			μs
t _{SU,STO}	STOP condition set-up time	0.6			μs
t _{BUF}	Bus free time between a STOP and START condition	1.3			μs

¹For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32G Reference Manual. ²The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}). ³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 4).

Table 3.20. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Тур	Мах	Unit
f _{SCL}	SCL clock frequency	0		1000 ¹	kHz
t _{LOW}	SCL clock low time	0.5			μs
t _{HIGH}	SCL clock high time	0.26			μs
t _{SU,DAT}	SDA set-up time	50			ns
t _{HD,DAT}	SDA hold time	8			ns
t _{SU,STA}	Repeated START condition set-up time	0.26			μs
t _{HD,STA}	(Repeated) START condition hold time	0.26			μs
t _{SU,STO}	STOP condition set-up time	0.26			μs
t _{BUF}	Bus free time between a STOP and START condition	0.5			μs

¹For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32G Reference Manual.

3.15 Digital Peripherals

Table 3.21. Digital Peripherals

Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{USART}	USART current	USART idle current, clock en- abled		7.5		μΑ/ MHz
I _{UART}	UART current	UART idle current, clock en- abled		5.63		µA/ MHz
I _{LEUART}	LEUART current	LEUART idle current, clock en- abled		150		nA
I _{I2C}	I2C current	I2C idle current, clock enabled		6.25		μΑ/ MHz
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		8.75		μΑ/ MHz
I _{LETIMER}	LETIMER current	LETIMER idle current, clock enabled		150		nA



Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{PCNT}	PCNT current	PCNT idle current, clock en- abled		100		nA
I _{RTC}	RTC current	RTC idle current, clock enabled		100		nA
I _{AES}	AES current	AES idle current, clock enabled		2.5		µA/ MHz
I _{GPIO}	GPIO current	GPIO idle current, clock en- abled		5.31		μΑ/ MHz
I _{EBI}	EBI current	EBI idle current, clock enabled		1.56		μΑ/ MHz
I _{PRS}	PRS current	PRS idle current		2,81		μA/ MHz
I _{DMA}	DMA current	Clock enable		8.12		µA/ MHz

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32G280.

4.1 Pinout

The *EFM32G280* pinout is shown in Figure 4.1 (p. 48) and Table 4.1 (p. 48). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32G280 Pinout (top view, not to scale)

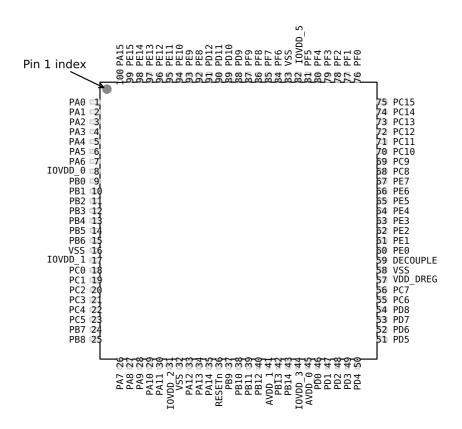


Table 4.1. Device Pinout

	QFP100 Pin# and Name	Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
1	PA0		EBI_AD09 #0	TIM0_CC0 #0/1	I2C0_SDA #0	
2	PA1		EBI_AD10 #0	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0
3	PA2		EBI_AD11 #0	TIM0_CC2 #0/1		CMU_CLK0 #0



	QFP100 Pin# and Name		Pin Altern	ate Functionality / [Description	
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
4	PA3		EBI_AD12 #0	TIM0_CDTI0 #0	U0_TX #2	
5	PA4		EBI_AD13 #0	TIM0_CDTI1 #0	U0_RX #2	
6	PA5		EBI_AD14 #0	TIM0_CDTI2 #0	LEU1_TX #1	
7	PA6		EBI_AD15 #0		LEU1_RX #1	
8	IOVDD_0	Digital IO power supply 0.				
9	PB0			TIM1_CC0 #2		
10	PB1			TIM1_CC1 #2		
11	PB2			TIM1_CC2 #2		
12	PB3			PCNT1_S0IN #1	US2_TX #1	
13	PB4			PCNT1_S1IN #1	US2_RX #1	
14	PB5				US2_CLK #1	
15	PB6				US2_CS #1	
16	VSS	Ground.				
17	IOVDD_1	Digital IO power supply 1.				
18	PC0	ACMP0_CH0		PCNT0_S0IN #2	US1_TX #0	
19	PC1	ACMP0_CH1		PCNT0_S1IN #2	US1_RX #0	
20	PC2	ACMP0_CH2			US2_TX #0	
21	PC3	ACMP0_CH3			US2_RX #0	
22	PC4	ACMP0_CH4		LETIM0_OUT0 #3 PCNT1_S0IN #0	US2_CLK #0	
23	PC5	ACMP0_CH5		LETIM0_OUT1 #3 PCNT1_S1IN #0	US2_CS #0	
24	PB7	LFXTAL_P			US1_CLK #0	
25	PB8	LFXTAL_N			US1_CS #0	
26	PA7					
27	PA8			TIM2_CC0 #0		
28	PA9			TIM2_CC1 #0		
29	PA10			TIM2_CC2 #0		
30	PA11					
31	IOVDD_2	Digital IO power supply 2.				
32	VSS	Ground.				
33	PA12			TIM2_CC0 #1		
34	PA13			TIM2_CC1 #1		
35	PA14			TIM2_CC2 #1		
36	RESETn	Reset input, active low. To apply an external reset that reset is released.	source to this pin, it is re-	quired to only drive this pin	low during reset, and let th	e internal pull-up ensure
37	PB9					
38	PB10					
39	PB11	DAC0_OUT0		LETIM0_OUT0 #1		
40	PB12	DAC0_OUT1		LETIM0_OUT1 #1		
	I	1		I	1	



	QFP100 Pin# and Name	Pin Alternate Functionality / Description							
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other			
41	AVDD_1	Analog power supply 1.	·						
42	PB13	HFXTAL_P			LEU0_TX #1				
43	PB14	HFXTAL_N			LEU0_RX #1				
44	IOVDD_3	Digital IO power supply 3.		I					
45	AVDD_0	Analog power supply 0.							
46	PD0	ADC0_CH0		PCNT2_S0IN #0	US1_TX #1				
47	PD1	ADC0_CH1		TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1				
48	PD2	ADC0_CH2		TIM0_CC1 #3	US1_CLK #1				
49	PD3	ADC0_CH3		TIM0_CC2 #3	US1_CS #1				
50	PD4	ADC0_CH4			LEU0_TX #0				
51	PD5	ADC0_CH5	<u> </u>		LEU0_RX #0				
52	PD6	ADC0_CH6		LETIM0_OUT0 #0	I2C0_SDA #1				
53	PD7	ADC0_CH7		LETIM0_OUT1 #0	I2C0_SCL #1				
54	PD8					CMU_CLK1 #1			
55	PC6	ACMP0_CH6			LEU1_TX #0 I2C0_SDA #2				
56	PC7	ACMP0_CH7			LEU1_RX #0 I2C0_SCL #2				
57	VDD_DREG	Power supply for on-chip	voltage regulator.	1					
58	VSS	Ground.							
59	DECOUPLE	Decouple output for on-ch	ip voltage regulator. An e	xternal capacitance of size	C _{DECOUPLE} is required at the	nis pin.			
60	PE0			PCNT0_S0IN #1	U0_TX #1				
61	PE1			PCNT0_S1IN #1	U0_RX #1				
62	PE2					ACMP0_O #1			
63	PE3					ACMP1_O #1			
64	PE4				US0_CS #1				
65	PE5				US0_CLK #1				
66	PE6				US0_RX #1				
67	PE7				US0_TX #1				
68	PC8	ACMP1_CH0		TIM2_CC0 #2	US0_CS #2				
69	PC9	ACMP1_CH1		TIM2_CC1 #2	US0_CLK #2				
70	PC10	ACMP1_CH2		TIM2_CC2 #2	US0_RX #2				
71	PC11	ACMP1_CH3			US0_TX #2				
72	PC12	ACMP1_CH4				CMU_CLK0 #1			
73	PC13	ACMP1_CH5		TIM0_CDTI0 #1/3 TIM1_CC0 #0 PCNT0_S0IN #0					
74	PC14	ACMP1_CH6		TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0	U0_TX #3				
75	PC15	ACMP1_CH7		TIM0_CDTI2 #1/3 TIM1_CC2 #0	U0_RX #3	DBG_SWO #1			



	QFP100 Pin# and Name		Pin Alternate Functionality / Description								
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other					
76	PF0			LETIM0_OUT0 #2		DBG_SWCLK #0/1					
77	PF1			LETIM0_OUT1 #2		DBG_SWDIO #0/1					
78	PF2		EBI_ARDY #0			ACMP1_O #0 DBG_SWO #0					
79	PF3		EBI_ALE #0	TIM0_CDTI0 #2							
80	PF4		EBI_WEn #0	TIM0_CDTI1 #2							
81	PF5		EBI_REn #0	TIM0_CDTI2 #2							
82	IOVDD_5	Digital IO power supply 5.									
83	VSS	Ground.									
84	PF6			TIM0_CC0 #2	U0_TX #0						
85	PF7			TIM0_CC1 #2	U0_RX #0						
86	PF8			TIM0_CC2 #2							
87	PF9										
88	PD9		EBI_CS0 #0								
89	PD10		EBI_CS1 #0								
90	PD11		EBI_CS2 #0								
91	PD12		EBI_CS3 #0								
92	PE8		EBI_AD00 #0	PCNT2_S0IN #1							
93	PE9		EBI_AD01 #0	PCNT2_S1IN #1							
94	PE10		EBI_AD02 #0	TIM1_CC0 #1	US0_TX #0	BOOT_TX					
95	PE11		EBI_AD03 #0	TIM1_CC1 #1	US0_RX #0	BOOT_RX					
96	PE12		EBI_AD04 #0	TIM1_CC2 #1	US0_CLK #0						
97	PE13		EBI_AD05 #0		US0_CS #0	ACMP0_O #0					
98	PE14		EBI_AD06 #0		LEU0_TX #2						
99	PE15		EBI_AD07 #0		LEU0_RX #2						
100	PA15		EBI_AD08 #0								

4.2 Alternate Functionality Pinout

A wide selection of alternate functionality is available for multiplexing to various pins. This is shown in Table 4.2 (p. 51). The table shows the name of the alternate functionality in the first column, followed by columns showing the possible LOCATION bitfield settings.

Note

Some functionality, such as analog interfaces, do not have alternate settings or a LOCA-TION bitfield. In these cases, the pinout is shown in the column corresponding to LOCA-TION 0.

Table 4.2. Alternate functionality overview

Alternate		LOCA	TION		
Functionality	0 1		2	3	Description
ACMP0_CH0	PC0				Analog comparator ACMP0, channel 0.

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Alternate	LOCATION					
Functionality	0	1	2	3	Description	
ACMP0_CH1	PC1				Analog comparator ACMP0, channel 1.	
ACMP0_CH2	PC2				Analog comparator ACMP0, channel 2.	
ACMP0_CH3	PC3				Analog comparator ACMP0, channel 3.	
ACMP0_CH4	PC4				Analog comparator ACMP0, channel 4.	
ACMP0_CH5	PC5				Analog comparator ACMP0, channel 5.	
ACMP0_CH6	PC6				Analog comparator ACMP0, channel 6.	
ACMP0_CH7	PC7				Analog comparator ACMP0, channel 7.	
ACMP0_O	PE13	PE2			Analog comparator ACMP0, digital output.	
ACMP1_CH0	PC8				Analog comparator ACMP1, channel 0.	
ACMP1_CH1	PC9				Analog comparator ACMP1, channel 1.	
ACMP1_CH2	PC10				Analog comparator ACMP1, channel 2.	
ACMP1_CH3	PC11				Analog comparator ACMP1, channel 3.	
ACMP1_CH4	PC12				Analog comparator ACMP1, channel 4.	
ACMP1_CH5	PC13				Analog comparator ACMP1, channel 5.	
ACMP1_CH6	PC14				Analog comparator ACMP1, channel 6.	
ACMP1_CH7	PC15				Analog comparator ACMP1, channel 7.	
ACMP1_O	PF2	PE3			Analog comparator ACMP1, digital output.	
ADC0_CH0	PD0				Analog to digital converter ADC0, input channel number 0.	
ADC0_CH1	PD1				Analog to digital converter ADC0, input channel number 1.	
ADC0_CH2	PD2				Analog to digital converter ADC0, input channel number 2.	
ADC0_CH3	PD3				Analog to digital converter ADC0, input channel number 3.	
ADC0_CH4	PD4				Analog to digital converter ADC0, input channel number 4.	
ADC0 CH5	PD5				Analog to digital converter ADC0, input channel number 5.	
ADC0_CH6	PD6				Analog to digital converter ADC0, input channel number 6.	
ADC0_CH7	PD7				Analog to digital converter ADC0, input channel number 7.	
BOOT RX	PE11				Bootloader RX.	
BOOT TX	PE10				Bootloader TX.	
CMU_CLK0	PA2	PC12			Clock Management Unit, clock output number 0.	
CMU_CLK1	PA1	PD8			Clock Management Unit, clock output number 1.	
DAC0_OUT0	PB11				Digital to Analog Converter DAC0 output channel number 0.	
DAC0_OUT1	PB12				Digital to Analog Converter DAC0 output channel number 1.	
5/100_0011					Debug-interface Serial Wire clock input.	
DBG_SWCLK	PF0	PF0			Note that this function is enabled to pin out of reset, and has a built-in pull down.	
					Debug-interface Serial Wire data input / output.	
DBG_SWDIO	PF1	PF1			Note that this function is enabled to pin out of reset, and has a built-in pull up	
					Debug-interface Serial Wire viewer Output.	
DBG_SWO	PF2	PC15			Note that this function is not enabled after reset, and must be enabled by software to be used.	
EBI_AD00	PE8				External Bus Interface (EBI) address and data input / output pin 00.	
EBI_AD01	PE9				External Bus Interface (EBI) address and data input / output pin 01.	
EBI_AD02	PE10				External Bus Interface (EBI) address and data input / output pin 02.	
EBI_AD03	PE11				External Bus Interface (EBI) address and data input / output pin 03.	

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Alternate		LOCA	TION		
Functionality	0	1	2	3	Description
EBI_AD04	PE12				External Bus Interface (EBI) address and data input / output pin 04.
EBI_AD05	PE13				External Bus Interface (EBI) address and data input / output pin 05.
EBI_AD06	PE14				External Bus Interface (EBI) address and data input / output pin 06.
EBI_AD07	PE15				External Bus Interface (EBI) address and data input / output pin 07.
EBI_AD08	PA15				External Bus Interface (EBI) address and data input / output pin 08.
EBI_AD09	PA0				External Bus Interface (EBI) address and data input / output pin 09.
EBI_AD10	PA1				External Bus Interface (EBI) address and data input / output pin 10.
EBI_AD11	PA2				External Bus Interface (EBI) address and data input / output pin 11.
EBI_AD12	PA3				External Bus Interface (EBI) address and data input / output pin 12.
EBI_AD13	PA4				External Bus Interface (EBI) address and data input / output pin 13.
EBI_AD14	PA5				External Bus Interface (EBI) address and data input / output pin 14.
EBI_AD15	PA6				External Bus Interface (EBI) address and data input / output pin 15.
EBI_ALE	PF3				External Bus Interface (EBI) Address Latch Enable output.
EBI_ARDY	PF2				External Bus Interface (EBI) Hardware Ready Control input.
EBI_CS0	PD9				External Bus Interface (EBI) Chip Select output 0.
EBI_CS1	PD10				External Bus Interface (EBI) Chip Select output 1.
EBI_CS2	PD11				External Bus Interface (EBI) Chip Select output 2.
EBI_CS3	PD12				External Bus Interface (EBI) Chip Select output 3.
EBI_REn	PF5				External Bus Interface (EBI) Read Enable output.
EBI_WEn	PF4				External Bus Interface (EBI) Write Enable output.
HFXTAL_N	PB14				High Frequency Crystal negative pin. Also used as external optional clock in- put pin.
HFXTAL_P	PB13				High Frequency Crystal positive pin.
I2C0_SCL	PA1	PD7	PC7		I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6	PC6		I2C0 Serial Data input / output.
LETIM0_OUT0	PD6	PB11	PF0	PC4	Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7	PB12	PF1	PC5	Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14	PE15		LEUART0 Receive input.
LEU0_TX	PD4	PB13	PE14		LEUART0 Transmit output. Also used as receive input in half duplex commu- nication.
LEU1_RX	PC7	PA6			LEUART1 Receive input.
LEU1_TX	PC6	PA5			LEUART1 Transmit output. Also used as receive input in half duplex commu- nication.
LFXTAL_N	PB8				Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7				Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN	PC13	PE0	PC0		Pulse Counter PCNT0 input number 0.
PCNT0_S1IN	PC14	PE1	PC1		Pulse Counter PCNT0 input number 1.
PCNT1_S0IN	PC4	PB3			Pulse Counter PCNT1 input number 0.
PCNT1_S1IN	PC5	PB4			Pulse Counter PCNT1 input number 1.
PCNT2_S0IN	PD0	PE8			Pulse Counter PCNT2 input number 0.
PCNT2_S1IN	PD1	PE9			Pulse Counter PCNT2 input number 1.
TIM0_CC0	PA0	PA0	PF6	PD1	Timer 0 Capture Compare input / output channel 0.



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Alternate		LOCA	TION		
Functionality	0	1	2	3	Description
TIM0_CC1	PA1	PA1	PF7	PD2	Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	PA2	PA2	PF8	PD3	Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI0	PA3	PC13	PF3	PC13	Timer 0 Complimentary Deat Time Insertion channel 0.
TIM0_CDTI1	PA4	PC14	PF4	PC14	Timer 0 Complimentary Deat Time Insertion channel 1.
TIM0_CDTI2	PA5	PC15	PF5	PC15	Timer 0 Complimentary Deat Time Insertion channel 2.
TIM1_CC0	PC13	PE10	PB0		Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11	PB1		Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12	PB2		Timer 1 Capture Compare input / output channel 2.
TIM2_CC0	PA8	PA12	PC8		Timer 2 Capture Compare input / output channel 0.
TIM2_CC1	PA9	PA13	PC9		Timer 2 Capture Compare input / output channel 1.
TIM2_CC2	PA10	PA14	PC10		Timer 2 Capture Compare input / output channel 2.
U0_RX	PF7	PE1	PA4	PC15	UART0 Receive input.
U0_TX	PF6	PE0	PA3	PC14	UART0 Transmit output. Also used as receive input in half duplex communi- cation.
US0_CLK	PE12	PE5	PC9		USART0 clock input / output.
US0_CS	PE13	PE4	PC8		USART0 chip select input / output.
US0_RX	PE11	PE6	PC10		USART0 Asynchronous Receive.
		1 20	1010		USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX	PE10	PE7	PC11		USART0 Asynchronous Transmit. Also used as receive input in half duplex communication.
					USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7	PD2			USART1 clock input / output.
US1_CS	PB8	PD3			USART1 chip select input / output.
US1 RX	PC1	PD1			USART1 Asynchronous Receive.
					USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX	PC0	PD0			USART1 Asynchronous Transmit. Also used as receive input in half duplex communication.
					USART1 Synchronous mode Master Output / Slave Input (MOSI).
US2_CLK	PC4	PB5			USART2 clock input / output.
US2_CS	PC5	PB6			USART2 chip select input / output.
US2_RX	PC3	PB4			USART2 Asynchronous Receive.
					USART2 Synchronous mode Master Input / Slave Output (MISO).
US2_TX	PC2	PB3			USART2 Asynchronous Transmit. Also used as receive input in half duplex communication.
					USART2 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

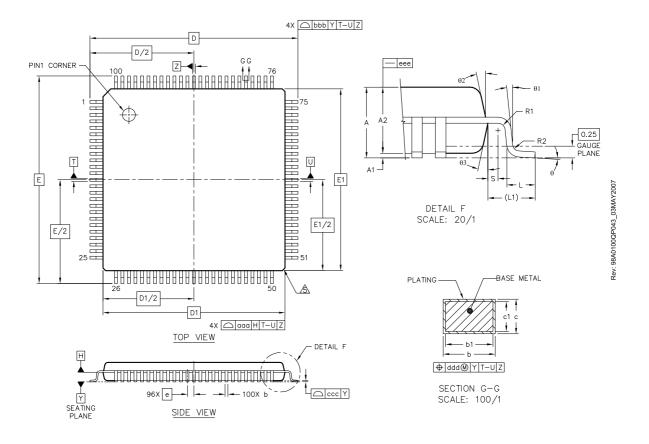
The specific GPIO pins available in *EFM32G280* is shown in Table 4.3 (p. 55). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	PA14	PA13	PA12	PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	-	PB14	PB13	PB12	PB11	PB10	PB9	PB8	PB7	PB6	PB5	PB4	PB3	PB2	PB1	PB0
Port C	PC15	PC14	PC13	PC12	PC11	PC10	PC9	PC8	PC7	PC6	PC5	PC4	PC3	PC2	PC1	PC0
Port D	-	-	-	PD12	PD11	PD10	PD9	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	PE7	PE6	PE5	PE4	PE3	PE2	PE1	PE0
Port F	-	-	-	-	-	-	PF9	PF8	PF7	PF6	PF5	PF4	PF3	PF2	PF1	PF0

4.4 LQFP100 Package

Figure 4.2. LQFP100



Note:

- 1. Datum 'T', 'U' and 'Z' to be determined at datum plane 'H'.
- 2. Datum 'D' and 'E' to be determined at seating plane datum 'Y'.
- 3. Dimension 'D1' and 'E1' do not include mold protrusions. Allowable protrusion is 0.25 per side. Dimensions 'D1' and 'E1' do include mold mismatch and are determined at datum plane datum 'H'.
- 4. Dimension 'b' does not include dambar protrusion. Allowable dambar protrusion shall not cause the lead width to exceed the maximum 'b' dimension by more than 0.08 mm. Dambar can not be located on the lower radius or the foot. Minimum space between protrusion and an adjacent lead is 0.07 mm
- 5. Exact shape of each corner is optional.

Table 4.4. LQFP100 (Dimensions in mm)

		SYMBOL	MIN	NOM	MAX		
total thickness		A			1.6		
stand off	A1	0.05		0.15			
mold thickness		A2	1.35	1.4	1.45		
lead width (plating)	b	0.17	0.2	0.27		
lead width		b1	0.17		0.23		
L/F thickness (platin	g)	с	0.09		0.2		
lead thickness		c1	0.09		0.16		
	х	D		16 BSC			
	У	E		16 BSC			
body size	х	D1		14 BSC			
body size	У	E1		14 BSC			
lead pitch	lead pitch			0.5 BSC			
		L	0.45	0.6	0.75		
footprint		L1		1 REF			
		θ	0°	3.5°	7°		
		θ1	0°				
		θ2	11°	12°	13°		
		θ3	11°	12°	13°		
		R1	0.08				
		R1	0.08		0.2		
				0.2			
package edge tolerar	nce	aaa		0.2			
lead edge tolerance	e	bbb		0.2			
coplanarity		ссс		0.08			
lead offset		ddd		0.08			
mold flatness		eee		0.05			

The LQFP100 Package uses Nickel-Palladium-Gold preplated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see: http://www.silabs.com/support/quality/pages/default.aspx

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. LQFP100 PCB Land Pattern

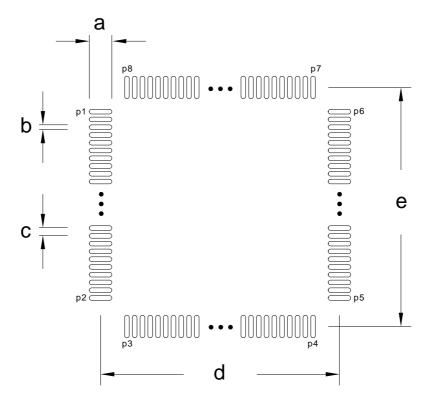


Table 5.1. QFP100 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
а	1.45	P1	1	P6	75
b	0.30	P2	25	P7	76
с	0.50	P3	26	P8	100
d	15.40	P4	50	-	-
е	15.40	P5	51	-	-



Figure 5.2. LQFP100 PCB Solder Mask

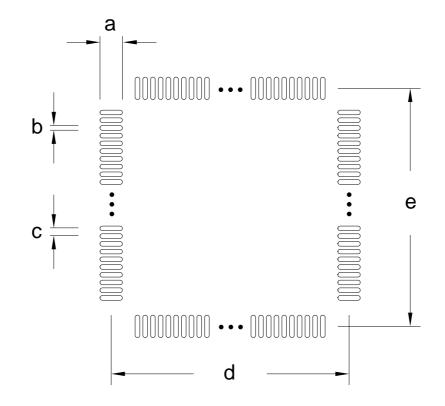


Table 5.2. QFP100 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
а	1.57
b	0.42
с	0.50
d	15.40
e	15.40



Figure 5.3. LQFP100 PCB Stencil Design

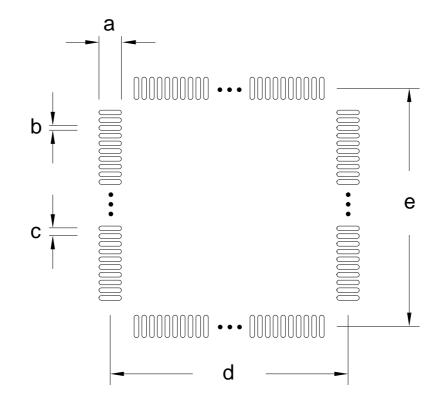


Table 5.3. QFP100 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
а	1.35
b	0.20
c	0.50
d	15.40
e	15.40

- 1. The drawings are not to scale.
- 2. All dimensions are in millimeters.
- 3. All drawings are subject to change without notice.
- 4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
- 5. Stencil thickness 0.125 mm.
- 6. For detailed pin-positioning, see Figure 4.2 (p. 55) .

5.2 Soldering Information

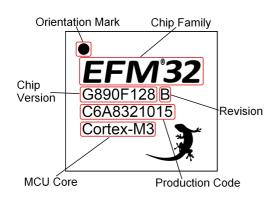
The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 60) .

6.3 Errata

Please see the errata document for EFM32G280 for description and resolution of device erratas. This document is available in Simplicity Studio and online at: http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

7 Revision History

7.1 Revision 1.90

May 22nd, 2015

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Added AUXHFRCO to block diagram and Electrical Characteristics.

Updated HFRCO table in the Electrical Characteristics section.

Updated EM0, EM2, EM3, and EM4 maximum current specifications in the Electrical Characteristics section.

Updated the Output Low Voltage maximum for sinking 20 mA with VDD = 3.0 V in the Electrical Characteristics section.

Updated the Input Leakage Current maximum in the Electrical Characteristics section.

Updated the minimum and maximum frequency specifications for the LFRCO, HFRCO, and AUXHFRCO in the Electrical Characteristics section.

Updated the maximum current consumption of the HFRCO in the Electrical Characteristics section.

Updated the maximum current consumption of the HFRCO in the Electrical Characteristics section.

Added some minimum ADC SNR, SNDR, and SFDR specifications in the Electrical Characteristics section.

Added some minimum and maximum ADC offset voltage, DNL, and INL specifications in the Electrical Characteristics section.

Added maximum DAC current specifications in the Electrical Characteristics section.

Added maximum ACMP current and maximum and minimum offset voltage specifications in the Electrical Characteristics section.

Added maximum VCMP current and updated typical VCMP current specifications in the Electrical Characteristics section.

Updated references to energyAware Designer to Configurator.

7.2 Revision 1.80

July 2nd, 2014

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated current consumption.

Updated transition between energy modes.

Updated power management data.

Updated GPIO data.

Updated LFXO, HFXO, HFRCO and ULFRCO data.

Updated LFRCO and HFRCO plots.

Updated ACMP data.

7.3 Revision 1.71

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.4 Revision 1.70

September 30th, 2013

Added I2C characterization data.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.5 Revision 1.60

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.50

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 1.40

February 27th, 2012

Updated Power Management section.

Corrected operating voltage from 1.8 V to 1.85 V.

Corrected TGRAD_{ADCTH} parameter.

Corrected LQFP100 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.8 Revision 1.30

May 20th, 2011

Updated LFXO load capacitance section.

7.9 Revision 1.20

December 17th, 2010

Increased max storage temperature.

Added data for <150°C and <70°C on Flash data retention.

Changed latch-up sensitivity test description.

Added IO leakage current.

Updated ESD CDM value.

Added Flash current consumption.

Updated HFRCO data.

Updated LFRCO data.

Added graph for ADC Absolute Offset over temperature.

Added graph for ADC Temperature sensor readout.

7.10 Revision 1.11

November 17th, 2010

Corrected maximum DAC clock speed for continuous mode.

Added DAC sample-hold mode voltage drift rate.

Added pulse widths detected by the HFXO glitch detector.

Added power sequencing information to Power Management section.

7.11 Revision 1.10

September 13th, 2010

Corrected number of GPIO pins.

Added typical values for $R_{ADCFILT}$ and $C_{ADCFILT}$.

Added two conditions for DAC clock frequency; one for sample/hold and one for sample/off.

Added RoHS information and specified leadframe/solderballs material.

Added Serial Bootloader to feature list and system summary.

Updated ADC characterization data.

Updated DAC characterization data.

Updated RCO characterization data.

Updated ACMP characterization data.

Updated VCMP characterization data.

7.12 Revision 1.00

April 23rd, 2010

ADC_VCM line removed.

Added pinout illustration and additional pinout table.

Changed "Errata" chapter. Errata description moved to separate document.

Document changed status from "Preliminary".

Updated "Electrical Characteristics" chapter.

7.13 Revision 0.85

February 19th, 2010

Renamed DBG_SWV pin to DBG_SWO.

7.14 Revision 0.83

January 25th, 2010 Updated errata section. Specified flash word width in Section 3.7 (p. 18) . Added Capacitive Sense Internal Resistor values in Section 3.12 (p. 43) .

7.15 Revision 0.82

December 9th, 2009

Incorrect pin 0 removed from Table 4.1 (p. 48) .

Updated contact information.

ADC current consumption numbers updated in Section 3.10 (p. 32) .

7.16 Revision 0.81

November 20th, 2009

Section 3.1 (p. 9) updated.

Storage temperature in Section 3.2 (p. 9) updated.

Temperature coefficient of band-gap reference in Section 3.6 (p. 17) added.

Erase times in Section 3.7 (p. 18) updated.

Definitions of DNL and INL added in Figure 3.27 (p. 36) and Figure 3.28 (p. 37) .

Current consumption of digital peripherals added in Section 3.15 (p. 46).

Package information in Section 4.4 (p. 55) corrected.

Updated errata section.

7.17 Revision 0.80

Initial preliminary revision, October 19th, 2009

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Table of Contents

1. Ordering Information	. 2
2. System Summary	. 3
2.1. System Introduction	
2.2. Configuration Summary	
2.3. Memory Map 3. Electrical Characteristics	6
3.1. Test Conditions	
3.2. Absolute Maximum Ratings	
3.3. General Operating Conditions	ğ
3.4. Current Consumption	
3.5. Transition between Energy Modes	17
3.6. Power Management	17
3.7. Flash	
3.8. General Purpose Input Output	
3.9. Oscillators	27
3.10. Analog Digital Converter (ADC)	32
3.11. Digital Analog Converter (DAC)	41
3.12. Analog Comparator (ACMP)	43
3.13. Voltage Comparator (VCMP)	45
3.14. I2C	45
3.15. Digital Peripherals	
4. Pinout and Package	48
4.1. Pinout	
4.2. Alternate Functionality Pinout	51
4.3. GPIO Pinout Overview	
4.4. LQFP100 Package	
5. PCB Layout and Soldering	57
5.1. Recommended PCB Layout	57
5.2. Soldering Information	59
6. Chip Marking, Revision and Errata	
6.1. Chip Marking	60
6.2. Revision	
6.3. Errata	
7. Revision History	61
7.2. Revision 1.80	61
7.3. Revision 1.71	
7.4. Revision 1.70	
7.5. Revision 1.60	
7.6. Revision 1.50	
7.7. Revision 1.40	
7.8. Revision 1.30	63
7.9. Revision 1.20	
7.10. Revision 1.11	
7.11. Revision 1.10	
7.12. Revision 1.00	64
7.13. Revision 0.85	64
7.14. Revision 0.83	64
7.15. Revision 0.82	64
7.16. Revision 0.81	64
7.17. Revision 0.80	
A. Disclaimer and Trademarks	
A.1. Disclaimer	
A.2. Trademark Information	
B. Contact Information	
В.1	67

List of Figures

2.1. Block Diagram	. 3
2.2. EFM32G280 Memory Map with largest RAM and Flash sizes	8
3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 28	
MHz	11
3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21	
MHz	11
3.3. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 14	
MHz	12
3.4. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 11	
MHz	12
3.5. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 7	
MHz	
3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28 MHz	
3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz	
3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz	
3.9. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11 MHz	
3.10. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 7 MHz	. 15
3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO	. 16
3.12. EM3 current consumption	
3.13. EM4 current consumption.	17
3.14. Typical Low-Level Output Current, 2V Supply Voltage	
3.15. Typical High-Level Output Current, 2V Supply Voltage	. 22
3.16. Typical Low-Level Output Current, 3V Supply Voltage	23
3.17. Typical High-Level Output Current, 3V Supply Voltage	. 24
3.18. Typical Low-Level Output Current, 3.8V Supply Voltage	
3.19. Typical High-Level Output Current, 3.8V Supply Voltage	26
3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage	
3.21. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature	
3.22. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature	
3.23. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature	
3.24. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature	
3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature	. 31
3.26. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature	. 31
3.27. Integral Non-Linearity (INL)	
3.28. Differential Non-Linearity (DNL)	
3.29. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C	
3.30. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C	39
3.31. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C	
3.32. ADC Absolute Offset, Common Mode = Vdd /2	. 41
3.33. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V	41
3.34. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1	44
4.1. EFM32G280 Pinout (top view, not to scale)	
4.2. LQFP100	
5.1. LQFP100 PCB Land Pattern	
5.2. LQFP100 PCB Solder Mask	
5.3. LQFP100 PCB Stencil Design	
6.1. Example Chip Marking (top view)	. 60

List of Tables

1.1. Ordering Information	. 2
2.1. Configuration Summary	. 6
3.1. Absolute Maximum Ratings	. 9
3.2. General Operating Conditions	. 9
3.3. Current Consumption	
3.4. Energy Modes Transitions	
3.5. Power Management	
3.6. Flash	18
3.7. GPIO	
3.8. LFXO	27
3.9. HFXO	
3.10. LFRCO	
3.11. HFRCO	
3.12. AUXHFRCO	
3.13. ULFRCO	
3.14. ADC	
3.15. DAC	
3.16. ACMP	
3.17. VCMP	
3.18. I2C Standard-mode (Sm)	45
3.19. I2C Fast-mode (Fm)	
3.20. I2C Fast-mode Plus (Fm+)	
3.21. Digital Peripherals	
4.1. Device Pinout	
4.2. Alternate functionality overview	
4.3. GPIO Pinout	
4.4. LQFP100 (Dimensions in mm)	
5.1. QFP100 PCB Land Pattern Dimensions (Dimensions in mm)	57
5.2. QFP100 PCB Solder Mask Dimensions (Dimensions in mm)	
5.3. QFP100 PCB Stencil Design Dimensions (Dimensions in mm)	59



List of Equations

3.1. Total ACMP Active Current	43
3.2. VCMP Trigger Level as a Function of Level Setting	45

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